

Chemical Twinning in Zintl Phases[†]

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In the systems Ba/Mg/(Si, Ge), two new ternary Zintl phases with the compositions BaMg₄Si₃ and BaMg₄Ge₃ were found and structurally characterized. Both compounds are isotypic and crystallize with a new structure type [BaMg₄Si₃, *P4/mmm*, *Z* = 1, *a* = 4.6115(9) Å, *c* = 8.615(2) Å; BaMg₄Ge₃, *P4/mmm*, *Z* = 1, *a* = 4.6335(8) Å, *c* = 8.746(2) Å]. The anionic partial structure is built of X₂⁶⁻ dumbbells and isolated X⁴⁻ ions (X = Si, Ge), and the structure can be described according to the Zintl–Klemm–Busmann concept with the formulation (Ba²⁺)(Mg²⁺)₄[X₂⁶⁻][X⁴⁻]. The BaMg₄X₃ structure can also be described as a result of the fusion of the structures of Mg₂X and BaMg₂X₂. In this regard, BaMg₄Si₃ and BaMg₄Ge₃ are very striking examples of chemical twinning.

Introduction

One of the most important and demanding tasks for a chemist is to ascertain the essential features of structure–property relationships. A very simple structure can be described in several ways. The chemist has to choose the best one, depending on which microscopic feature he wants to point out. For example, rock salt has a very simple structure but it can be described in at least three different ways: as two interpenetrating fcc networks of sodium and chlorine, as an fcc packing of sodiums with the octahedral holes occupied by chlorines and vice versa, and as edge-sharing octahedra of sodium filled with chlorines and vice versa. All descriptions are equivalent, but each one points out a different characteristic of the rock salt structure. The different descriptions should be simple and general; thus, they should show as many relationships as possible to related structures, and they should be useful in explaining physical properties.¹ Andersson and Hyde^{1,2} as well as Parthé,³ in their pioneering work, have shown that complex structures can be described by combining simple building blocks in a manner that is reminiscent of the twinning of crystals, though on a smaller scale. This approach is called “chemical twinning”¹ or intergrowth.³ The building blocks, which are part of the unit cells, are combined according to “twinning laws” as translation, reflection, and rotation.¹

We have collected some examples where this simple approach can be used in describing the structures of Zintl phases.^{4,5} In this work, we will report a very beautiful and illustrative example of “chemical twinning” using the two new Zintl phases BaMg₄Si₃ and BaMg₄Ge₃, which crystallize in a novel structure type.

The new phase BaMg₄X₃ extends the hitherto known ternary compounds BaMgX,^{6,7} BaMg₂X₂,^{8,9} Ba₅Mg₁₈X₁₃,¹⁰ and Ba₂Mg₃Si₄¹¹ of the system Ba/Mg/X (X = Si, Ge) by one other interesting representative.

Experimental Section

The compounds were synthesized from the pure elements (Mg pieces, Fluka, 99.8%; Ba rods, Alfa, 99.9%; Si powder, Alfa, 99.99%; Ge lumps, Alfa, 99.9999%), which were sealed under argon atmosphere in niobium ampules and transferred to a furnace under vacuum.

BaMg₄Si₃ decomposes peritectically above 1300 K to Ba₅Mg₁₈Si₁₃ and a melt of Mg/Si. Consequently, pure phase material was not produced from stoichiometric amounts of the elements. The maximum yield of crystalline BaMg₄Si₃ is obtained by cooling a melt of the composition Ba:Mg:Si = 1:2:4 from 1350 K at 50 K 1 h. The XRD powder pattern indicates the presence of BaSi₂, apart from the main product BaMg₄Si₃. The brittle material has a silvery metallic luster and is sensitive to air and moisture.

BaMg₄Ge₃ decomposes peritectically above 1180 K to Ba₅Mg₁₈Ge₁₃ and a melt of Mg/Ge. The highest yield of BaMg₄Ge₃ is obtained by heating a stoichiometric mixture of the elements up to 1120 K. After the system is cooled at about 200 K/h, a brittle material having a silvery metallic luster is produced. The XRD powder pattern indicates the presence of traces of BaMg₂Ge₂, apart from the main product BaMg₄Ge₃. The product is exceptionally sensitive to air and moisture and decomposes in a few seconds to a yellow-orange powder, which probably contains amorphous GeO.

The single crystals of BaMg₄Si₃ and BaMg₄Ge₃ (black fragments with a metallic luster) were examined on STOE IPSD and STADI4 four-circle diffractometers, respectively, both operating with graphite monochromators and Mo K α radiation. The diffraction data were collected in the angular ranges 5° < 2 θ < 50° (oscillation method, φ = 0–181°, $\Delta\varphi$ = 1.0°) and 2° < 2 θ < 60° (ω – θ scan, 40 steps, $\Delta\omega$ = 0.03°), respectively. The diffraction data of BaMg₄Ge₃ were empirically corrected for absorption (ψ scan). The Laue symmetry is *4/mmm*, and there are no systematic extinctions allowing for the space groups *P4nm*, *P422*, *P42m*, *P4m2*, and *P4/mmm*. The refinement of the unit cell yielded the following lattice parameters: *a* = 4.6115(9) Å, *c* = 8.615(2) Å for BaMg₄Si₃ and *a* = 4.6335(8) Å, *c* = 8.746(2)

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Table 1. Crystallographic Data for BaMg₄Si₃ and BaMg₄Ge₃

chem. formula	BaMg ₄ Si ₃	BaMg ₄ Ge ₃
fw	318.85	452.35
space group	<i>P4/mmm</i> (No. 123)	<i>P4/mmm</i> (No. 123)
<i>a</i> , Å	4.6115(9)	4.6335(8)
<i>b</i> , Å	4.6115(9)	4.6335(8)
<i>c</i> , Å	8.615(2)	8.746(2)
cell vol. Å ³	183.21(6)	187.77(7)
<i>Z</i>	1	1
temp., K	298	298
wavelength, Å	0.710 73	0.710 73
ρ_{calcd} , g·cm ⁻³	2.890	4.000
abs coeff, mm ⁻¹	6.135	17.282
reliability factors ^a		
<i>R</i> (<i>F</i> _o)	0.017	0.022
<i>R</i> _w (<i>F</i> _o ²)	0.040	0.054

$$^a R = \sum ||F_o| - |F_c|| / \sum |F_o|. \quad ^b R_w(F_o^2) = [\sum w(F_o^2 - F_c^2) / \sum w(F_o^2)]^{1/2}.$$

Table 2. Wyckoff Sites, Atomic Coordinates, and Equivalent Isotropic Displacement Parameters (Å²) for BaMg₄Si₃

atom	Wyckoff site	<i>x</i>	<i>y</i>	<i>z</i>	<i>U</i> (iso)
Ba	1 <i>a</i>	0	0	0	0.0108(4)
Mg	4 <i>i</i>	0	1/2	0.3176(2)	0.0121(5)
Si(1)	1 <i>b</i>	0	0	1/2	0.0103(7)
Si(2)	2 <i>h</i>	1/2	1/2	0.1426(2)	0.0099(5)

Table 3. Selected Interatomic Distances (Å) for BaMg₄Si₃

Ba–Si(2)	3.4847(9)	×8	Mg–Si(2)	2.755(2)	×2
Ba–Mg	3.579(2)	×8	Mg–Si(1)	2.790(1)	×2
Si(1)–Mg	2.790(1)	×8	Mg–Mg	3.142(4)	
Si(2)–Si(2)	2.458(4)		Mg–Mg	3.2608(6)	×4
Si(2)–Mg	2.755(2)	×4	Mg–Ba	3.579(2)	×2
Si(2)–Ba	3.4847(9)	×4			

Table 4. Wyckoff Sites, Atomic Coordinates, and Equivalent Isotropic Displacement Parameters (Å²) for BaMg₄Ge₃

atom	Wyckoff site	<i>x</i>	<i>y</i>	<i>z</i>	<i>U</i> (iso)
Ba	1 <i>a</i>	0	0	0	0.0149(2)
Mg	4 <i>i</i>	0	1/2	0.3188(2)	0.0164(4)
Ge(1)	1 <i>b</i>	0	0	1/2	0.0134(3)
Ge(2)	2 <i>h</i>	1/2	1/2	0.14723(6)	0.0138(2)

Table 5. Selected Interatomic Distances (Å) for BaMg₄Ge₃

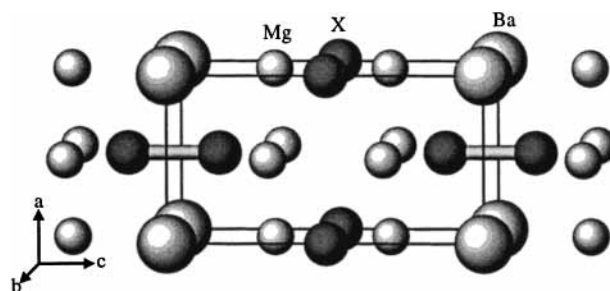
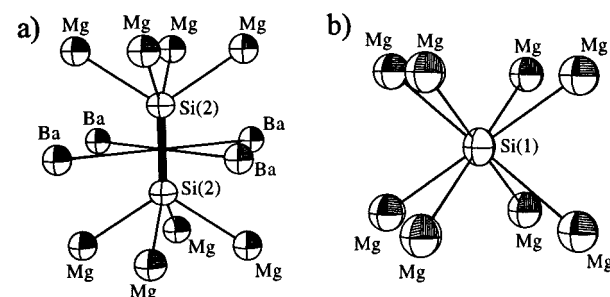
Ba–Ge(2)	3.5204(6)	×8	Mg–Ge(2)	2.7602(9)	×2
Ba–Mg	3.625(1)	×8	Mg–Ge(1)	2.8070(8)	×2
Ge(1)–Mg	2.8070(8)	×8	Mg–Mg	3.170(3)	
Ge(2)–Ge(2)	2.576(1)		Mg–Mg	3.2764(6)	×4
Ge(2)–Mg	2.7602(9)	×4	Mg–Ba	3.625(2)	×2
Ge(2)–Ba	3.5204(6)	×4			

Å for BaMg₄Ge₃. The structure of BaMg₄Si₃ was solved in *P4/mmm* using direct methods and refined by full-matrix least-squares *F*². The structure of BaMg₄Ge₃ was refined in *P4/mmm* (full-matrix least-squares *F*²) using the parameters of the isotypic BaMg₄Si₃. All atoms were anisotropically refined and the displacement parameters are all satisfactory in both structures. The final refined agreement parameters for the BaMg₄Si₃ and BaMg₄Ge₃ structures are given in Table 1. Atomic coordinates and selected interatomic distances are listed in Tables 2–5.

Structure and Discussion

BaMg₄Si₃ and BaMg₄Ge₃ are isotypic and crystallize within a novel structure type (Figure 1). The anionic partial structure is built of X₂ dumbbells and isolated X ions (X = Si, Ge). According to the Zintl–Klemm–Busmann concept,^{12,13} BaMg₄X₃ can be described by the formulation (Ba²⁺)(Mg²⁺)₄[X₂⁶⁻][X⁴⁻].

The dumbbells, formally X₂⁶⁻, show a cation coordination (Figure 2a) comparable to that found in the structure of BaMg₂X₂ (X = Si, Ge).^{8,9} The center of the X–X bond is coordinated by a square of Ba atoms. Together with magnesium,

**Figure 1.** Perspective view of the structure of BaMg₄X₃ (X = Si, Ge).**Figure 2.** Coordination of the Si₂⁶⁻ dumbbells (a) and isolated Si⁴⁻ anions (b) in BaMg₄Si₃.

a distorted square antiprism Ba₄Mg₄ is formed around the X atoms of the dumbbells. This basic building unit is quite typical for the coordination of terminal silicon or germanium atoms in even more extended Zintl anions found in compounds of the phase systems EA/Mg/(Li)/(Si, Ge).^{4,5,10,11} At 2.46 and 2.58 Å, the X–X distances are in the range of typical single-bond lengths for silicon and germanium, respectively. The isolated X atoms, formally X⁴⁻, are coordinated by eight magnesium atoms, forming a cube (Figure 2b), as in the structure of Mg₂X.^{14–17} Again the strong preference of magnesium for the coordination of highly charged silicon or germanium centers is evident. From a number of investigations, we already know that magnesium acts quite differently on Zintl anions than the heavier alkaline-earth metals Ca, Sr, and Ba. Thus, it is not surprising that, compared to the valence isoelectronic compounds Ba₅X₃ (Cr₅B₃ type; X = Si, Ge),^{18,19} a novel structure type is realized in BaMg₄X₃, just because of the different functionalities of the cation types.

Although both structures of Ba₅X₃ and BaMg₄X₃ are built of X₂ dumbbells and isolated X atoms, BaMg₄X₃ shows a much greater relationship to the structures of BaMg₂X₂ and Mg₂X than to that of Ba₅X₃. Actually, it is possible to derive the structures of BaMg₄X₃ just by fusing the structures of BaMg₂X₂ and Mg₂X (Figure 3). The lengths of the tetragonal *a* axes of BaMg₂X₂ and BaMg₄X₃ are nearly identical (4.65 and 4.61 Å for the Si compounds; 4.67 and 4.63 Å for the Ge compounds), and the values for the *c* axes of BaMg₄X₃ (8.62 and 8.75 Å observed for the Si and Ge compounds, respectively) calculated

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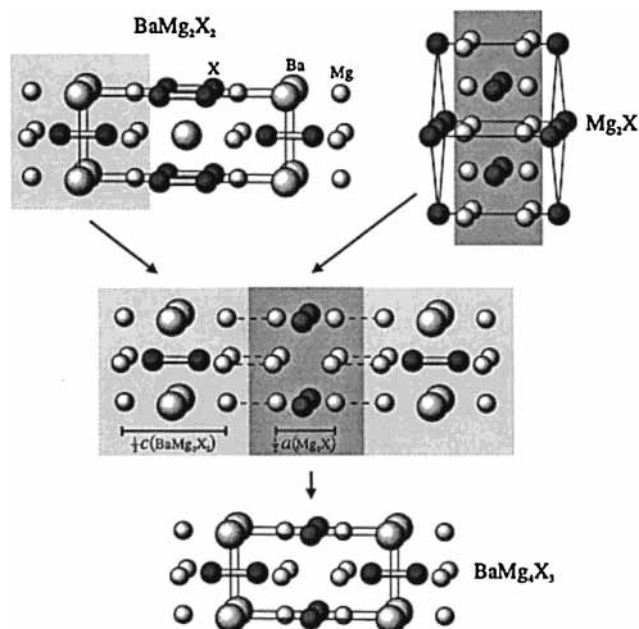


Figure 3. The $BaMg_4X_3$ structure ($X = Si, Ge$) showing chemical twinning. The marked sections of the $BaMg_2X_2$ and Mg_2X structures (top) fuse together, retaining the original dimensions (middle) and forming the daughter structure $BaMg_4X_3$ (bottom).

by adding the lattice parameters of $BaMg_2X_2$ and Mg_2X according to $c(BaMg_4X_3) = \frac{1}{2}a(Mg_2X) + \frac{1}{2}c(BaMg_2X_2)$

(leading to 8.71 and 8.86 Å, respectively) are equal within 0.1 Å to those observed. The discrepancy is due to a slight compression of the Mg_2X block along the c axis ($a/a' = 1.03$, compared with 1.0 for cubic Mg_2X). Thus, $BaMg_4X_3$ is a very nice example of chemical twinning in the sense of the descriptions of Andersson and Hyde,^{1,2} and Parthé.³

The “chemical twinning” reported for $BaMg_4Si_3$ and $BaMg_4Ge_3$ is a very beautiful example of how Nature can form complex structures by combining simple building blocks. The fusion of these building units retains the original distances, and it is possible to calculate the new lattice parameters simply by adding the original lengths of the parent structures. The structure of $BaMg_4Si_3$ and $BaMg_4Ge_3$ is the almost perfect topological fusing of the structures of Mg_2Si and $BaMg_2Si_2$ and of Mg_2Ge and $BaMg_2Ge_2$, respectively. Mg_2X and $BaMg_2X_2$ can be called the *parent structures* of $BaMg_4X_3$ ($X = Si, Ge$), which is therefore the *daughter structure*. We have shown that the “chemical twinning” approach is very powerful and intuitive and it can be used for predicting new structures.⁴

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Supporting Information Available: X-ray crystallographic files, in CIF format, for both refined structures. This material is available free of charge via the Internet at <http://pubs.acs.org>.

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